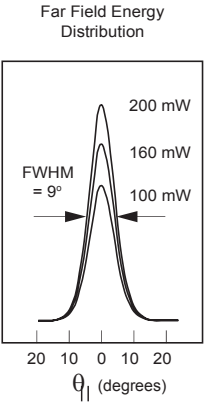
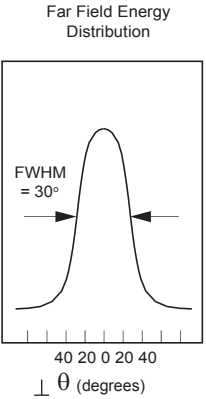
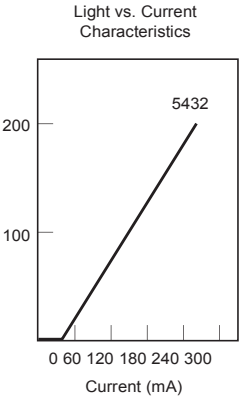


Parameter	Symbol	5432_-J1 Series			Unit
		n.	Typ.	Max.	
Laser Characteristics					
CW output power, kink-free ²	P _O	—	—	200	mW
Center wavelength	λ _c	—	(note ³)	—	
Spectral width ¹	Δ λ	—	3	5	nm
Slope efficiency	η _D = P _O /(I _{op} –I _{th})	0.75	1	—	mW/mA
Conversion efficiency	η = P _O /(I _{op} V _{op})	—	30	—	%
Emitting dimensions	W x H	—	3 x 1	—	μm
FWHM beam divergence					
Parallel to junction	θ _{//}	—	0.85	—	degrees
Perpendicular to junction	θ _⊥	—	30	—	degrees
Threshold current	I _{th}	—	35	45	mA
Operating current	I _{op}	—	270	300	
Operating voltage	V _{op}	—	(note ⁴)	—	4
Series resistance	R _s	—	4.5	6.5	Ω
Thermal resistance	R _{th}	—	60	—	°C/W
Recommended case temperature	T _c	-20	—	30	°C
Absolute Maximum Ratings					
Reverse voltage	V _{rl}	—	—	2.4	V
Case operating temperature	T _{op}	-20	—	50	°C
Storage temperature range	T _{stg}	-40	—	80	°C
Lead soldering temperature	T _{is}	—	—	250	°C (5 sec.)
Monitor Photodiode					
Sensitivity	—	0.1	—	20	μA/mW
Capacitance	—	—	6	—	pF
Breakdown voltage	V _{bd}	—	25	—	V
Operating voltage	V _{op}	—	10	—	V

Typical Optical Characteristics



Dimensions Diagrams

(Specifications in inches [mm] unless otherwise noted.)

Standard Tolerances

inches: x.xx = ± 0.02

x.xxx = ± 0.010

mm: x.x = ± 0.5

x.xx = ± 0.25

Package Style: TO-56 Window (J1)

Pinout	

Pin	Description
1	Laser cathode (-)
2	Laser anode, MPD cathode and case ground
3	Monitor photodiode anode (+)

